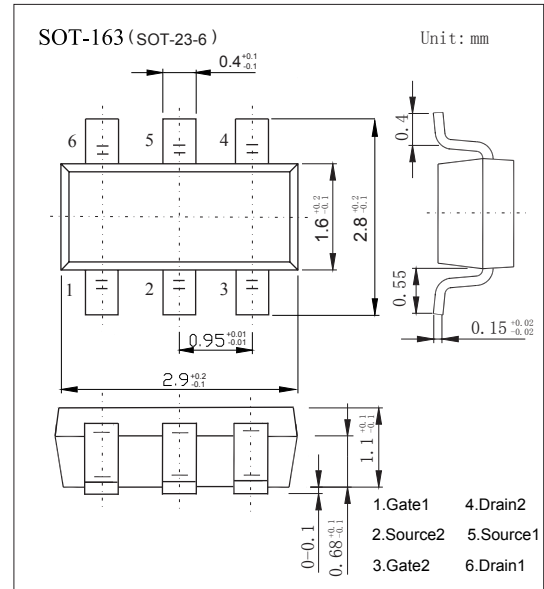
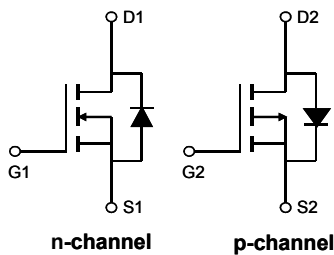


Complementary Trench MOSFET

AO6604

■ Features

- N-Channel: $V_{DS}=20V$ $I_D=3.4A$
 - $R_{DS(ON)} < 65m\Omega$ ($V_{GS} = 4.5V$)
 - $R_{DS(ON)} < 75m\Omega$ ($V_{GS} = 2.5V$)
 - $R_{DS(ON)} < 100m\Omega$ ($V_{GS} = 1.8V$)
- P-Channel: $V_{DS}=-20V$ $I_D=-2.5A$
 - $R_{DS(ON)} < 75m\Omega$ ($V_{GS} = -4.5V$)
 - $R_{DS(ON)} < 95m\Omega$ ($V_{GS} = -2.5V$)
 - $R_{DS(ON)} < 115m\Omega$ ($V_{GS} = -1.8V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V _{DS}	20	-20	V
Gate-Source Voltage	V _{GS}	±8		
Continuous Drain Current Ta = 25 °C Ta = 70 °C	I _D	3.4	-2.5	A
		2.5	-2	
Pulsed Drain Current	I _{DM}	13	-13	
Power Dissipation Ta = 25 °C Ta = 70 °C	P _D	1.1		W
		0.7		
Thermal Resistance.Junction- to-Ambient t ≤ 10s Steady-State	R _{thJA}	110		°C/W
		150		
Thermal Resistance.Junction- to-Lead Steady-State	R _{thJL}	80		
Junction Temperature	T _J	150		°C
Storage Temperature Range	T _{stg}	-55 to 150		

Complementary Trench MOSFET

AO6604

■ N-Channel Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
		V _{DS} =20V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μA	0.4	0.7	1	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =3.4A		51	65	mΩ
		V _{GS} =4.5V, I _D =3.4A T _J =125°C		68	85	
		V _{GS} =2.5V, I _D =3A		58	75	
		V _{GS} =1.8V, I _D =2A		68	100	
On State Drain Current	I _{D(on)}	V _{GS} =4.5V, V _{DS} =5V	13			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3.4A		16		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =10V, f=1MHz	205	260	320	pF
Output Capacitance	C _{oss}		33	48	63	
Reverse Transfer Capacitance	C _{rss}		16	27	38	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.5	3	4.5	Ω
Total Gate Charge (4.5V)	Q _g	V _{GS} =4.5V, V _{DS} =10V, I _D =3.4A		2.9	3.8	nC
Gate Source Charge	Q _{gs}			0.4		
Gate Drain Charge	Q _{gd}			0.6		
Turn-On DelayTime	t _{d(on)}	V _{GS} =5V, V _{DS} =10V, R _L =2.95 Ω, R _G =3 Ω		2.5		ns
Turn-On Rise Time	t _r			3.2		
Turn-Off DelayTime	t _{d(off)}			21		
Turn-Off Fall Time	t _f			3		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 3.4A, dI/dt= 100A/μs		14	19	nC
Body Diode Reverse Recovery Charge	Q _{rr}			3.8		
Maximum Body-Diode Continuous Current	I _S				1.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V		0.7	1	V

Complementary Trench MOSFET

AO6604

■ P-Channel Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
		V _{DS} =-20V, V _{GS} =0V, T _J =55°C			-5	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 μA	-0.4	-0.65	-1	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-2.5A		56	75	mΩ
		V _{GS} =-4.5V, I _D =-2.5A T _J =125°C		80	105	
		V _{GS} =-2.5V, I _D =-2A		70	95	
		V _{GS} =-1.8V, I _D =-1A		85	115	
On state drain current	I _{D(ON)}	V _{GS} =-4.5V, V _{DS} =-5V	-13			A
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-2.5A		13		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-10V, f=1MHz		560	745	pF
Output Capacitance	C _{oss}			80		
Reverse Transfer Capacitance	C _{rss}			70		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		15	23	Ω
Total Gate Charge (4.5V)	Q _g	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-2.5A		8.5	11	nC
Gate Source Charge	Q _{gs}			1.2		
Gate Drain Charge	Q _{gd}			2.1		
Turn-On DelayTime	t _{d(on)}	V _{GS} =-4.5V, V _{DS} =-10V, R _L =4 Ω, R _{GEN} =6 Ω		7.2		ns
Turn-On Rise Time	t _r			36		
Turn-Off DelayTime	t _{d(off)}			53		
Turn-Off Fall Time	t _f			56		
Body Diode Reverse Recovery Time	t _{rr}	I _F =-2.5A, dI/dt=100A/μs		37	49	nC
Body Diode Reverse Recovery Charge	Q _{rr}			27		
Maximum Body-Diode Continuous Current	I _S				-1.5	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V		-0.7	-1	V

Complementary Trench MOSFET

AO6604

■ N-Channel Typical Characteristics

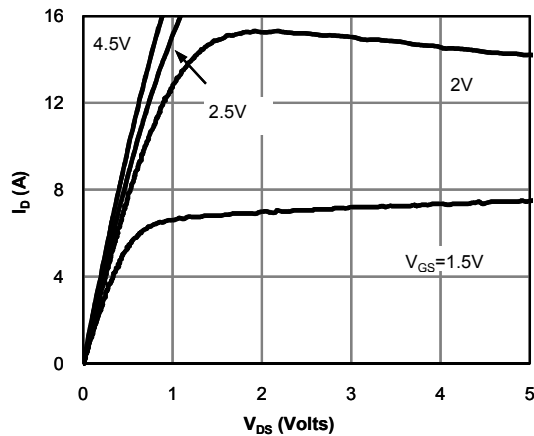


Fig 1: On-Region Characteristics (Note E)

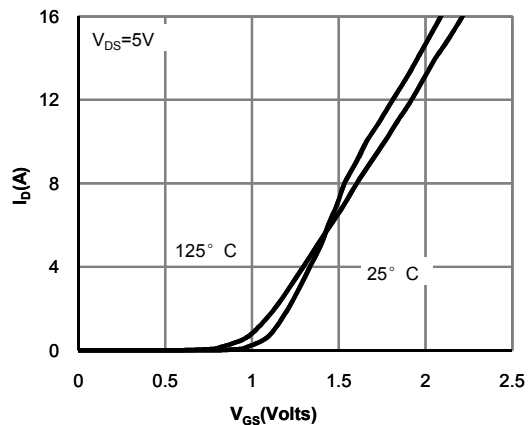


Figure 2: Transfer Characteristics (Note E)

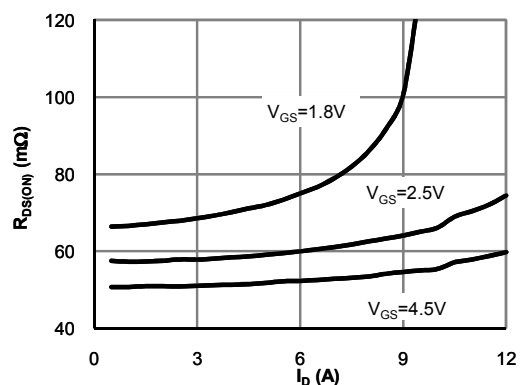


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

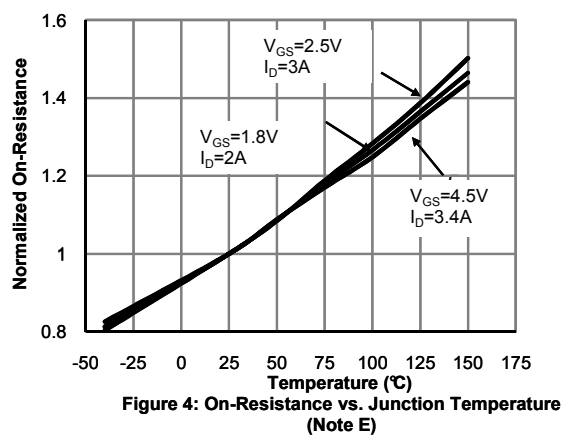


Figure 4: On-Resistance vs. Junction Temperature (Note E)

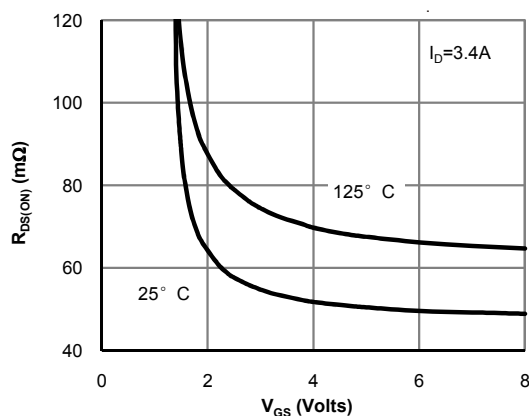


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

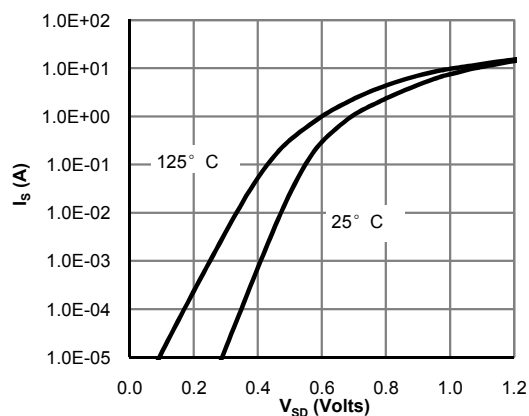


Figure 6: Body-Diode Characteristics (Note E)

Complementary Trench MOSFET

AO6604

■ N-Channel Typical Characteristics

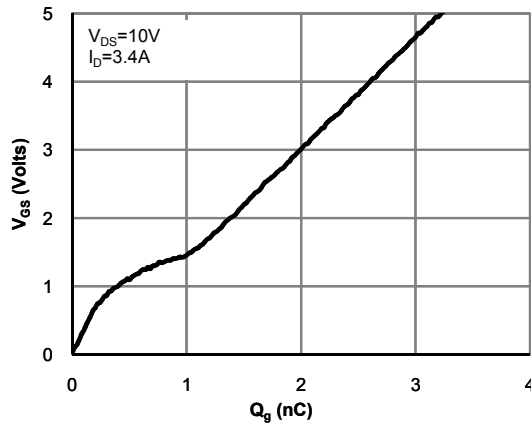


Figure 7: Gate-Charge Characteristics

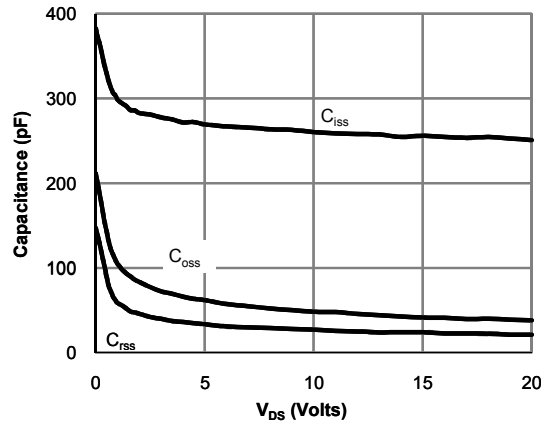


Figure 8: Capacitance Characteristics

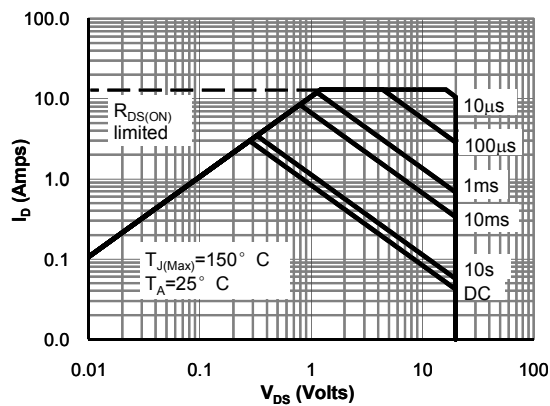


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

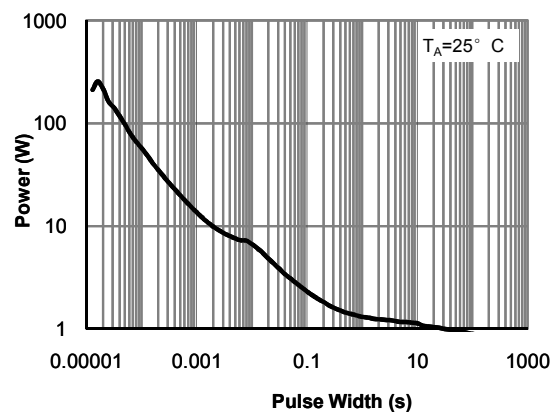


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

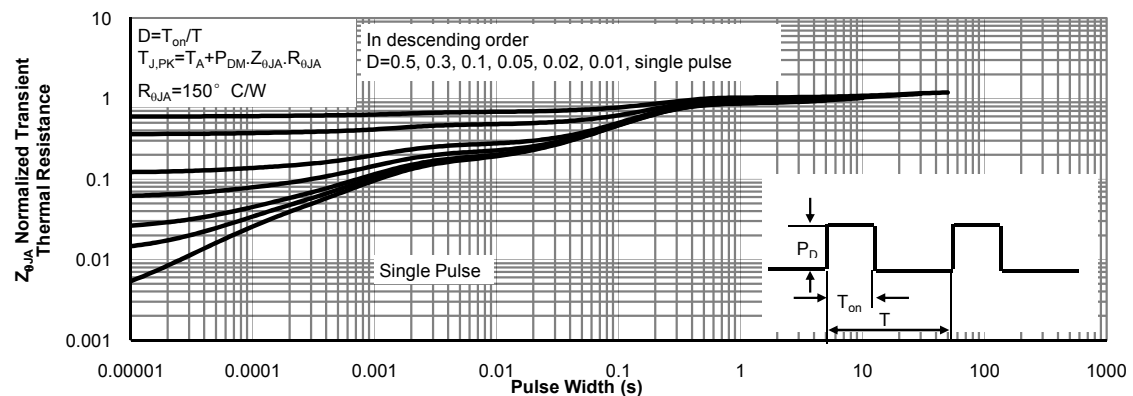


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Complementary Trench MOSFET

AO6604

■ P-Channel Typical Characteristics

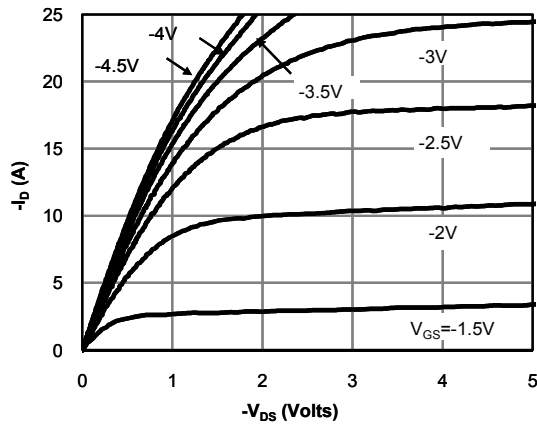


Fig 1: On-Region Characteristics (Note E)

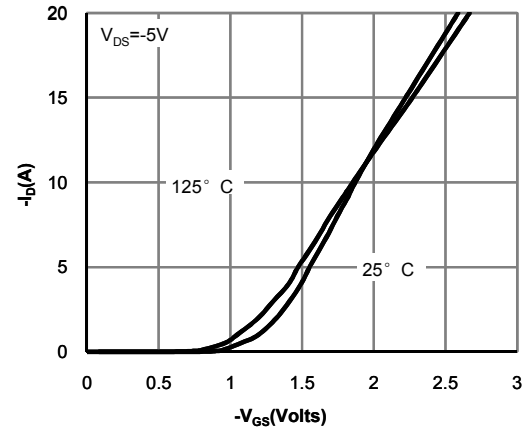


Figure 2: Transfer Characteristics (Note E)

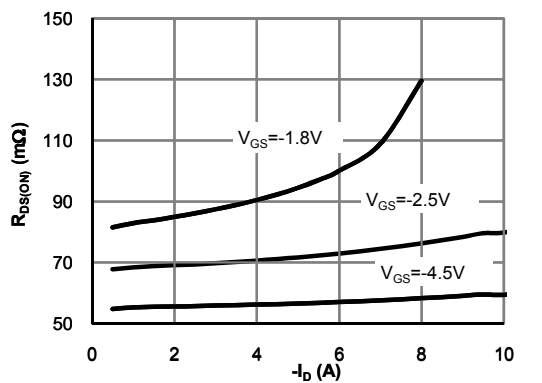


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

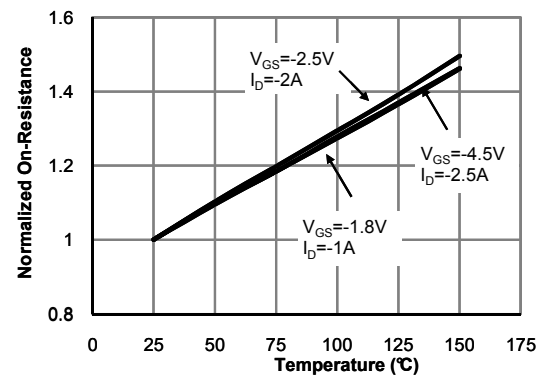


Figure 4: On-Resistance vs. Junction Temperature (Note E)

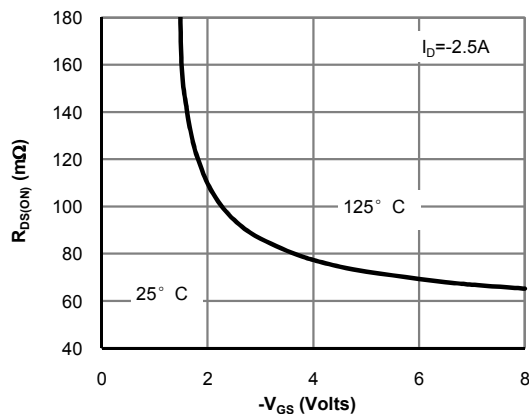


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

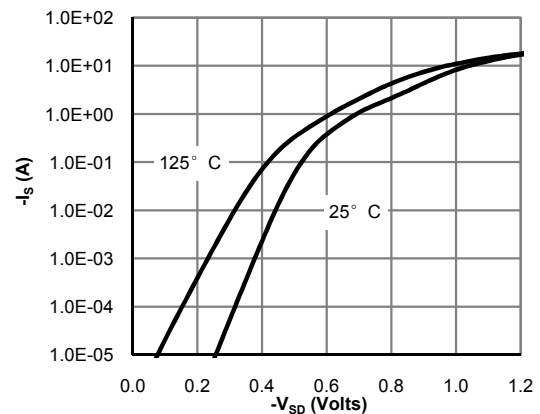


Figure 6: Body-Diode Characteristics (Note E)

Complementary Trench MOSFET

AO6604

■ P-Channel Typical Characteristics

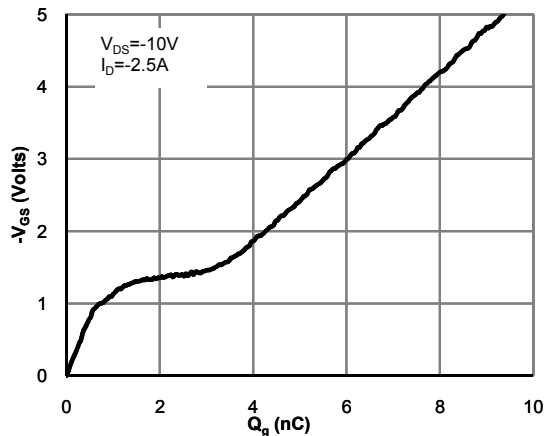


Figure 7: Gate-Charge Characteristics

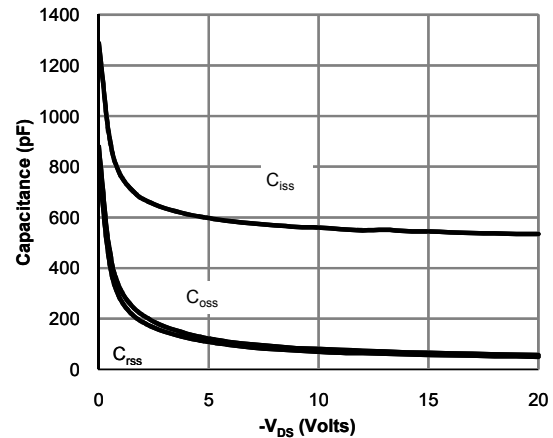


Figure 8: Capacitance Characteristics

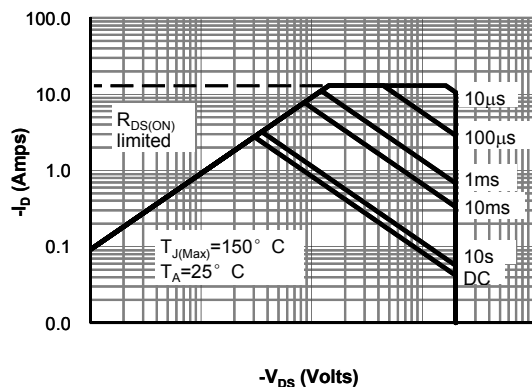


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

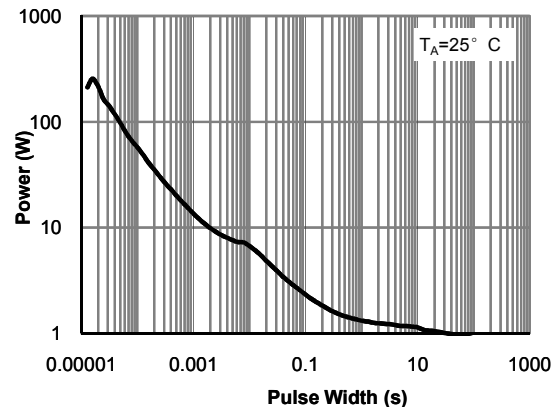


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

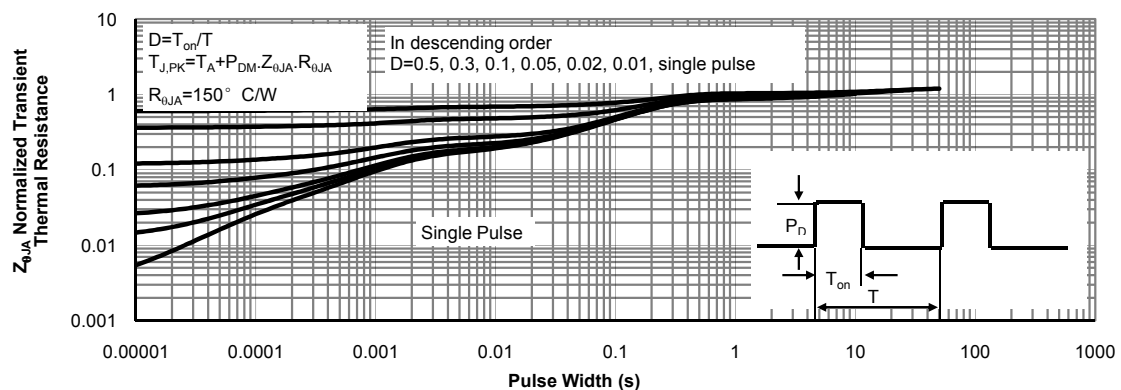


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)